NSN 5961-01-030-6409

Thyristor Semiconductor Device - Page 1 of 1

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Inclosure Material:

Metal

Overall Length:

2.577 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Mounting Method:

Threaded stud

Overall Width Across Flats:

1.062 inches

Thread Size:

0.250 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

300.0 repetitive peak off-state voltage and 300.0 repetitive peak reverse voltage and 400.0 reverse voltage, peak and 210.0 off-state voltage, rms total

Current Rating Per Characteristic:

70.00 amperes forward current, total rms universal and 1000.00 amperes peak forward surge current nanoamperes

Power Rating Per Characteristic:

5.0 watts small-signal input power, common-collector blank and 0.5 watts small-signal input power, common-collector universal

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius junction

Special Features:

Junction pattern arrangement: pnpn

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Thread Series Designator:

Unf

Terminal Type And Quantity:

3 insulated wire lead w/terminal lug and 1 threaded stud

Specification Data:

81349-mil-s-19500/203 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

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